Ordering number:EN3580A

NPN Epitaxial Planar Silicon Darlington Transistor

2SC4696

Driver Applications

Applications

· Motor drivers, printer hammer drivers.

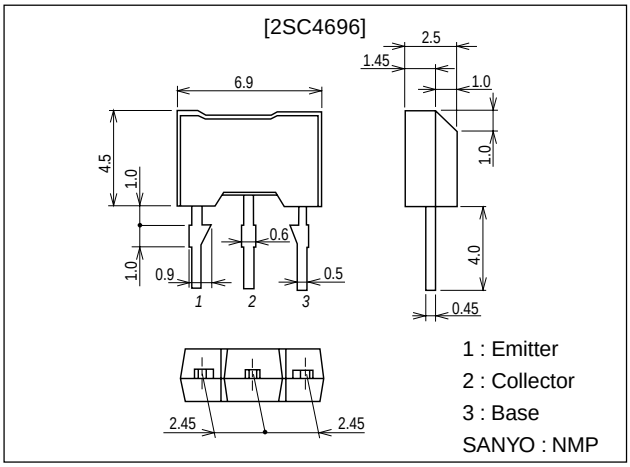
Features

· Darlington connection.
· On-chip Zener diode of 90±10V between collector and base.
· High DC current gain.
· High inductive load handling capability.

Package Dimensions

unit:mm

2064A



Specifications

Absolute Maximum Ratings at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}	With a low-voltage diode (90±10V)	80	V
Collector-to-Emitter Voltage	V_{CEO}	With a low-voltage diode (90±10V)	80	V
Emitter-to-Base Voltage	V_{EBO}		6	V
Collector Current	I_C		0.8	A
Collector Current (Pulse)	I_{CP}		1.5	A
Base Current	I_B		0.1	A
Collector Dissipation	P_C		1.0	W
Junction Temperature	Tj		150	˚C
Storage Temperature	Tstg		–55 to +150	˚C

Electrical Characteristics at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	V_{CB}=60V, I_E=0			10	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=5V, I_C=0			2	mA
DC Current Gain	h_{FE}	V_{CE}=3V, I_C=500mA	1000		20000	
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=500mA, I_B=1mA		0.95	1.5	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=500mA, I_B=1mA		1.5	2.0	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=100μA, I_E=0	80		100	V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=1mA, R_{BE}=∞	80		100	V
Inductive Load Handling Capability	Es/b	L=30mH, R_{BE}=100Ω	25			mJ

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Electrical Connection